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Tables of RADECS 2022 Papers

As usual, the Conference authors had a choice to submit their papers to the IEEE Conference Record of RADECS 2022 and/or to the IEEE Transactions on Nuclear Science Journal, each path of edition comprising its own Reviewing Committee.

As a result, a coherent Proceeding of the 2022 RADECS Conference results in the merging of two lists of papers which result from these paths.

79 papers resulted in Conference Record papers and 70 papers in IEEE Transactions on Nuclear Science papers. Both can be accessed in IEEEXplore, in the two different Sections.

Therefore, in the following we successively present two lists of papers ordered in two Sections, subsequently ordered by their place in the Conference Sessions.

Section I – Conference Papers

These papers were submitted to the Conference Review Committee and appear in the RADECS 2022 Conference Papers in IEEE Xplore (Conference Section, RADECS 2022).

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(Volume: 70, [Issue: 8](#) , Aug. 2023, part 1).

The August 2023 special issue of the IEEE Transactions on Nuclear Science contains 70 articles based on presentations made at the Conference and independently submitted to this Journal. They were reviewed independently of the Conference.

This Special issue can be reached at:

<https://ieeexplore.ieee.org/xpl/tocresult.jsp?isnumber=10221199>

For the completeness of the RADECS 2022 Conference Proceedings, the Conference Editors present in this Section II the list of these Journal papers ordered by their original sessions. The DOIs give easy access to this content which is reachable in the “Journal part” of IEEE Xplore.

The content comprises the papers as follows:

Session A: Single Event Effects: Mechanisms & Modeling

An Analysis of the Significance of the ^{14}N (n, p) ^{14}C Reaction for Single-Event Upsets Induced by Thermal Neutrons in SRAMs

A. Coronetti, R. García Alía, D. Lucsanyi, M. Letiche, M. Kastriotou, C. Cazzaniga, C. D. Frost, F. Saigné

DOI: [10.1109/TNS.2023.3239407](https://doi.org/10.1109/TNS.2023.3239407), p. 1634

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DOI: [10.1109/TNS.2023.3255169](https://doi.org/10.1109/TNS.2023.3255169), p. 1797

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DOI: [10.1109/TNS.2023.3295340](https://doi.org/10.1109/TNS.2023.3295340), p. 1755

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DOI: [10.1109/TNS.2023.3242829](https://doi.org/10.1109/TNS.2023.3242829), p. 1838

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DOI: [10.1109/TNS.2023.3266005](https://doi.org/10.1109/TNS.2023.3266005), p. 1724

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DOI: [10.1109/TNS.2022.3224356](https://doi.org/10.1109/TNS.2022.3224356), p. 1829

Single-Event Upsets for Single-Port and Two-Port SRAM Cells at the 5-nm FinFET Technology

N. J. Pieper, Y. Xiong, J. Pasternak, N. A. Dodds, D. R. Ball, B. L. Bhuvu

DOI: [10.1109/TNS.2023.3240979](https://doi.org/10.1109/TNS.2023.3240979), p. 1673

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DOI: [10.1109/TNS.2023.3246085](https://doi.org/10.1109/TNS.2023.3246085), p. 1687

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